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# HS-500

Low Noise High Voltage Switch

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## **Data Sheet**

Rev. 1.22

### **Features:**

- **Fast low noise switches (SPDT)**
- **Up to 500V switching voltage**
- **TTL/CMOS level control**
- **Floating up to 500V vs. GND**

### **Typical Applications:**

- **Ion Traps**
- **Beam Lines**
- **Fast Steerers**
- **Piezos**

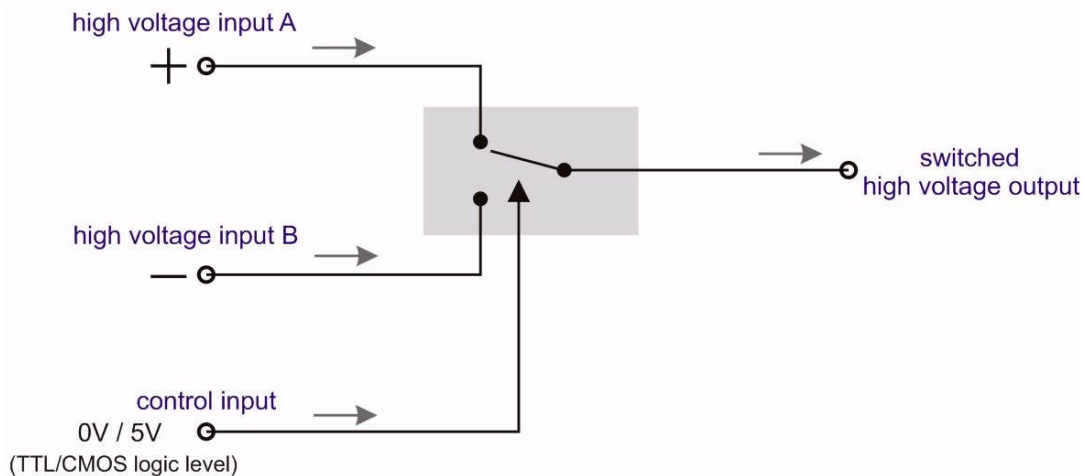
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## Purpose and Characteristics of the Device

Purpose of the HS series devices is the fast switching of electrodes, electrostatic lenses, beam deflectors or ion traps. Unlike DC power switches, the outputs expect capacitive loads. The outputs are optimized for high stability and very low noise. The HS series switches are housed in standard 19-inch rack-mount cases. They are available in single-channel or dual-channels versions. In the dual channel version two completely identical switches are housed inside the same case. These two switches are completely independent.



The following scheme displays a block diagram of the internal structure. The control input (BNC) defines the position of the internal high voltage switch, which connects either input A or input B to the output. A digital signal (TTL/CMOS level 0V/5V) may be applied to this control input at a rate between 0Hz (static operation) to 1.5 kHz. A three-position manual switch on the front side allows to override the digital control signal. The high voltage switching elements inside the device are implemented as MOSFET-transistors, allowing fast switching transitions in the order of 100ns and less. The non-selected input is isolated from the output by a high isolation resistance. Nominal loads from 0pF to 300pF may be connected.

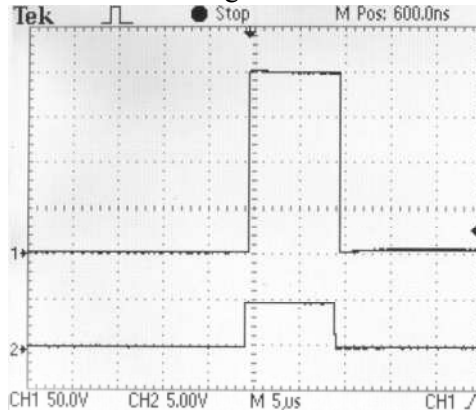


The applied supply voltages at inputs A and B obey a certain order: voltage at input A always needs to be more positive than voltage at input B. In general both input voltages may float up to +/-500V versus the case ground. However, for normal operation the voltage *difference* (A-B) should not exceed the rated voltage (500 Volts for HS-500).

### Application example: Generation of 10µs-duration positive 200V-pulse

The subsequent oscilloscope screen shot shows a typical application example. A control pulse of logic levels (high = 5V, low = 0V) is applied to the control input. High voltage inputs A and B were provided with an external voltage of 200V and 0V respectively. At the edges of the control signal the

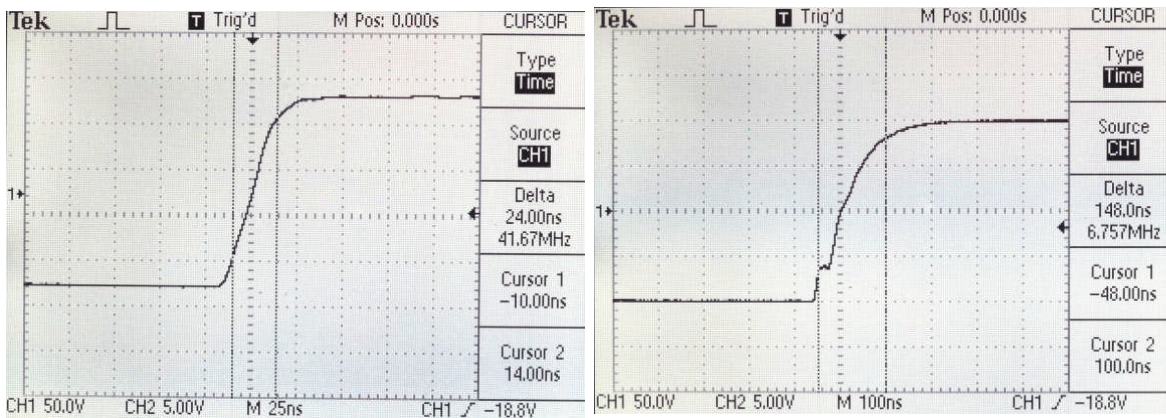
switch is triggered, and switches from 0V to 200V (trace 1: 50V/div.) and after 10 $\mu$ s back to 0 Volt. Trace 2 shows the control signal, being used to trigger the switch (trace 2: 5V/div.). A rectangular pulse results with steep slopes and constant-voltage static levels.



Oscilloscope screen shot of a positive 200V pulse,  $\Delta t = 10\mu$ s duration. The lower trace (trace 2) shows the digital control signal, trace 1 (upper trace) the output signal.

### Dynamic Response

As soon as the internal switch connects either input A or B to the output, the latter assumes the voltage on the respective input. There is a time constant related to each voltage transition, essentially given by the internal switch resistance (approx. 140  $\Omega$ ), the internal output current limit (approx.  $\pm 490$ mA) and the capacitive load on the output, including all cables to an experimental setup. The following oscilloscope screen shots show voltage step transitions observed at the output with small (17pF) and medium capacitive loads (300pF) for further illustration.



Left frame: voltage step of 200V with small capacitive load ( $C=17$ pF); transient rise time (10% to 90% of voltage step size) is in the order of 25ns. Right frame: positive voltage step of 200V with medium capacitive load of  $C = 300$ pF.

### Noise and Ripple

In contrast to other devices, the HS series devices feature a very low noise level. This makes them specially suited for ion traps, ion sources and low energy beam line applications. Each output exhibits a very low broadband noise (DC to 20MHz) of smaller than 350 $\mu$ V<sub>rms</sub> and a low ripple level (50Hz) smaller 50 $\mu$ V<sub>rms</sub>. In general the outputs are completely free of parasitic switching spikes in the RF region.

## Specifications

<b>Control Input</b>	typ.	max.	Conditions and remarks
required drive level	0V and 5V	-2V to +6V vs. GND	
threshold	2.4V		
input impedance	1k $\Omega$ // 6pF		
drive rate / switching rate		1.5kHz	
<b>Output Switch, static</b>			
static resistance from A or B to OUT "on"-state	140 $\Omega$	200 $\Omega$	I <sub>OUT</sub>   < 200mA
isolation resistance from A or B to OUT	>10M $\Omega$		voltage differences from A or B to OUT smaller or equal 200V
leakage currents from A or B to OUT	40nA*	200nA*	voltage differences from A or B to OUT smaller or equal 200V
intrinsic switch capacitance on OUT terminal vs. GND	25pF to 35pF		
Noise		350 $\mu$ V <sub>rms</sub>	
<b>Transfer characteristics</b>			
delay from control input change to output reaction	450ns		200V output step size (positive or negative going)
delay jitter	0.4ns rms		T = 25°C +/-1°C
max. pulse duration		infinite	
min. pulse duration	6.6 $\mu$ s		
Output rise or fall time, 10% to 90% step size	25ns 145ns		capacitive load of 17pF (probe head) capacitive load of 300pF
<b>Input Voltage Rating</b>			
Input A or B vs. GND		+/-500V	both polarities may be applied vs. GND
Voltage difference from A to B		+500V	input A always needs to be on more positive level with respect to B
Fuse rating	500mA fast		fuse replaceable on rear side
<b>Environmental Conditions</b>			
Magnetic Field		max. 5 mT	
Storage Temperature		-55 C° to +85 C°	
Operating Humidity & Temperature	noncondensing relative humidity up to 95% between temperatures of +10°C and +35°C.		
<b>Power Supply</b>	AC input voltage 230V <sub>AC</sub> at 50Hz. Fuse: medium fast blow 1.0A; Power Consumption 3.9W typ.		
<b>Case dimensions</b>	19.00" wide x 10" deep x 44mm height. Front-panel rack mount holes		

Note \*): Inputs A and B feature 200 M $\Omega$  resistors to ground for protection against charge up. Currents through these protection resistors add to the numbers mentioned above.

## Device Variety

<b>HS-200</b>	single or dual version	Output voltages of maximum 200V span <sup>1)</sup>
<b>HS-500</b>	single or dual version	Output voltages of maximum 500V span <sup>1)</sup>
<b>HS-1000 (obsolete)</b>	single or dual version	Output voltages of max. 1000V span <sup>1)</sup>

Note <sup>1)</sup>: span is the maximum voltage difference between positive and negative inputs A and B.